L Number	Hits	Search Text	DB	Time stamp
-	180	CMOS and FET and silicide and (self adj aligned adj silicide) and source and drain and gate	USPAT	2004/10/06 13:34
-	25	CMOS and FET and silicide and (self adj aligned adj silicide) and source and drain and gate and polysilicon and silicon and oxide and nitride and dielectric and compound and channel and region	USPAT	2004/10/06 13:47
-	1	("6589866").PN.	USPAT	2004/10/06 13:48
-	1	("6544827").PN.	USPAT	2004/10/06 13:49
-	1	("6534352").PN.	USPAT	2004/10/06 13:50
-	1	("6528362").PN.	USPAT	2004/10/06 13:50
-	1	("6492694").PN.	USPAT	2004/10/06 13:51
-	1	("6033963").PN.	USPAT	2004/10/06 13:51
-	1	(("6033963").PN.) and (CMOS or FET or PFET oe NFET or gate or metal or polysilicon or oxide or nitride or silicon or material or source or drain or self or aligned or silicide or structure or compound or tungsten or cobalt or nickel or dielectric or insulating or isolation or region or channel or active or area or overlying or sacrificial or opposite or transistor or spacer or sidewall or single otr band or gap)	USPAT	2004/10/06 14:20
-	1	(("6492694").PN.) and (CMOS or FET or PFET oe NFET or gate or metal or polysilicon or oxide or nitride or silicon or material or source or drain or self or aligned or silicide or structure or compound or tungsten or cobalt or nickel or dielectric or insulating or isolation or region or channel or active or area or overlying or sacrificial or opposite or transistor or spacer or sidewall or single otr band or gap)	USPAT	2004/10/06 14:21
-	1	(("6528362").PN.) and (CMOS or FET or PFET oe NFET or gate or metal or polysilicon or oxide or nitride or silicon or material or source or drain or self or aligned or silicide or structure or compound or tungsten or cobalt or nickel or dielectric or insulating or isolation or region or channel or active or area or overlying or sacrificial or opposite or transistor or spacer or sidewall or single otr band or gap)	USPAT	2004/10/06 14:21
-	1	(("6534352").PN.) and (CMOS or FET or PFET oe NFET or gate or metal or polysilicon or oxide or nitride or silicon or material or source or drain or self or aligned or silicide or structure or compound or tungsten or cobalt or nickel or dielectric or insulating or isolation or region or channel or active or area or overlying or sacrificial or opposite or transistor or spacer or sidewall or single otr band or gap)	USPAT	2004/10/06 14:22
-	1	(("6544827").PN.) and (CMOS or FET or PFET oe NFET or gate or metal or polysilicon or oxide or nitride or silicon or material or source or drain or self or aligned or silicide or structure or compound or tungsten or cobalt or nickel or dielectric or insulating or isolation or region or channel or active or area or overlying or sacrificial or opposite or transistor or spacer or sidewall or single otr band or gap)	USPAT	2004/10/06 14:23
-	1	(("6589866").PN.) and (CMOS or FET or PFET oe NFET or gate or metal or polysilicon or oxide or nitride or silicon or material or source or drain or self or aligned or silicide or structure or compound or tungsten or cobalt or nickel or dielectric or insulating or isolation or region or channel or active or area or overlying or sacrificial or opposite or transistor or spacer or sidewall or single otr band or gap)	USPAT	2004/10/06 14:25

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| | | 25 | (CMOS and FET and silicide and (self adj aligned adj silicide) and source and drain and gate and polysilicon and silicon and oxide and nitride and dielectric and compound and channel and region) and (CMOS or FET or PFET oe NFET or gate or metal or polysilicon or oxide or nitride or silicon or material or source or drain or self or aligned or silicide or structure or compound or tungsten or cobalt or nickel or dielectric or insulating or isolation or region or channel or active or area or overlying or sacrificial or opposite or transistor or spacer or sidewall or single otr band or gap) | USPAT | 2004/10/06 14:25 |